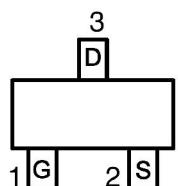
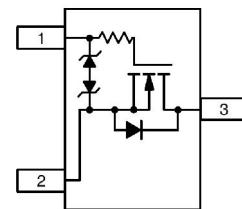


## Main Product Characteristics:

$V_{DSS}$	20V
$R_{DS(on)}$	3Ω
$I_D$	238mA



Pin Assignment



Schematic Diagram

## Features and Benefits:

- Low Gate Charge for Fast Switching
- Small 1.6 x 1.6 mm Footprint
- ESD Protected Gate
- Lead free product
- 150°C operating temperature



## Description:

It utilizes the latest trench processing techniques to achieve fast switching speed and short reverse recovery time. These features combine to make this design an extremely efficient and reliable device for use in Power Management Load Switch, Level Shift, Cell Phones, Media Players, Digital Cameras, PDA's, Video Games, Hand Held Computers, etc.

## Absolute Max Rating @ $T_A=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Max.	Units
ID	Continuous Drain Current ①	238	mA
IDM	Pulsed Drain Current ( $t_p \leq 10\mu\text{s}$ ) ②	714	
PD	Power Dissipation ③	300	mW
VDS	Drain-Source Voltage	20	V
VGS	Gate-to-Source Voltage	$\pm 10$	V
TJ TSTG	Operating Junction and Storage Temperature Range	-55 to 150	°C
T <sub>L</sub>	Lead Temperature for Soldering Purposes	260	
Isd	Continuous Source Current (Body Diode)	238	mA

## Thermal Resistance

Symbol	Characterizes	Value	Unit
$R_{\theta JA}$	Junction-to-Ambient (steady-state) ④	416	°C/W

**Electrical Characteristics @ $T_A=25^\circ\text{C}$  unless otherwise specified**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
BVDSS	Drain-to-Source breakdown voltage	20	—	—	V	VGS = 0V, ID = 100μA
RDS(on)	Static Drain-to-Source on-resistance	—	1.5	3.0	Ω	VGS = 4.5V, ID = 10mA
		—	2.2	3.5		VGS = 2.5V, ID = 10mA
VGS(th)	Gate threshold voltage	0.5	1.0	1.5	V	VDS = 3V, ID = 100μA
IDSS	Drain-to-Source leakage current	—	—	1.0	μA	VDS = 20V, VGS = 0V
IGSS	Gate-to-Source forward leakage	—	—	100	μA	VGS = 10V
	Gate-to-Source reverse leakage	-100	—	—		VGS = -10V
g <sub>FS</sub>	Forward Transconductance	—	50	—	mS	ID = 10mA, VDS=3V
td(on)	Turn-on delay time	—	13	—	ns	VGS=4.5V, VDS=5V, ID=10mA, RG=10Ω
tr	Rise time	—	15	—		
td(off)	Turn-Off delay time	—	98	—		
tf	Fall time	—	60	—		
C <sub>iss</sub>	Input capacitance	—	11.5	20	pF	VGS = 0V, VDS = 5V, f = 1.0MHz
C <sub>oss</sub>	Output capacitance	—	10	15		
C <sub>rss</sub>	Reverse transfer capacitance	—	3.5	6.0		

**Source-Drain Ratings and Characteristics**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
VSD	Diode Forward Voltage	—	0.66	0.8	V	IS=10mA, VGS=0V

**Notes:**

- ①The maximum current rating is limited by bond-wires.
- ②Repetitive rating; pulse width limited by max. junction temperature.
- ③The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④The value of  $R_{\theta JA}$  is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$

## Typical Electrical and Thermal Characteristics

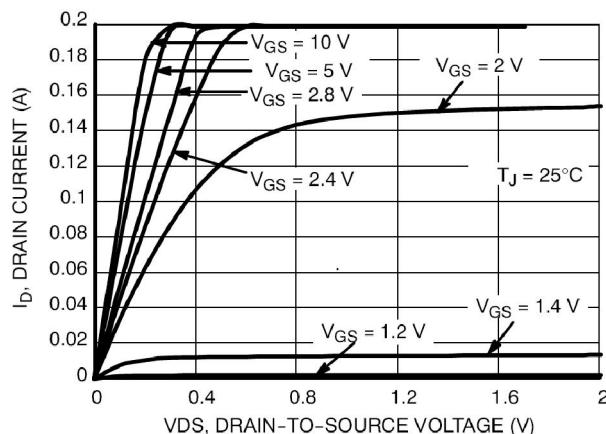


Figure 1. On-region Characteristics

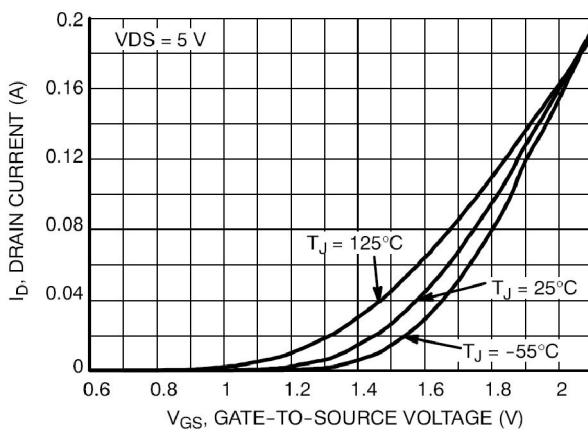


Figure 2. Transfer Characteristics

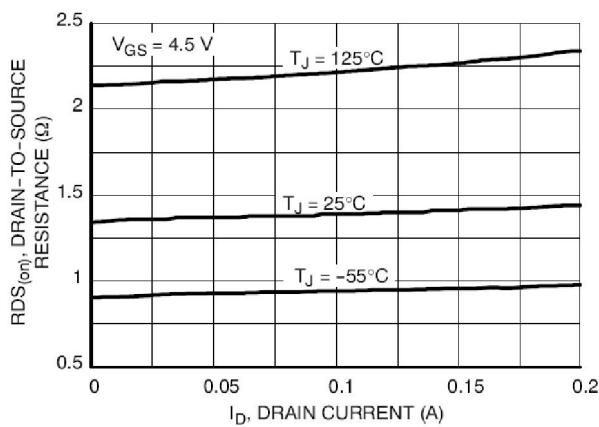


Figure 3. On-resistance versus Drain Current and Temperature

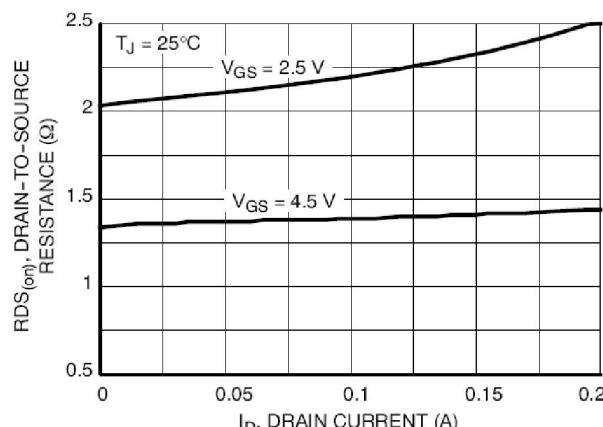


Figure 4. On-resistance versus Drain Current and Gate Voltage

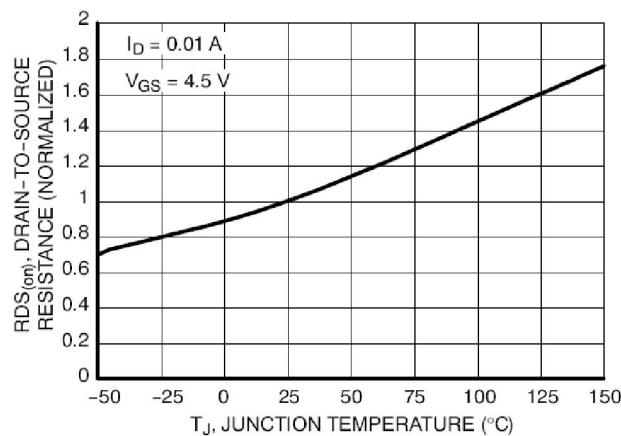


Figure 5. On-resistance Variation with Temperature

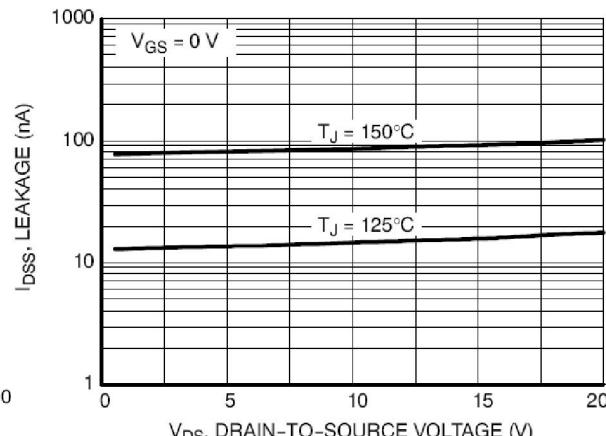
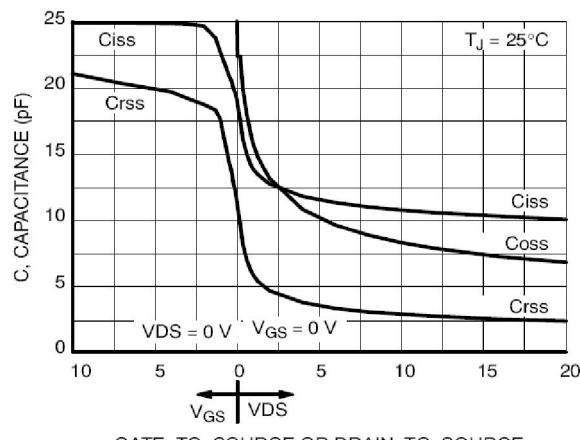


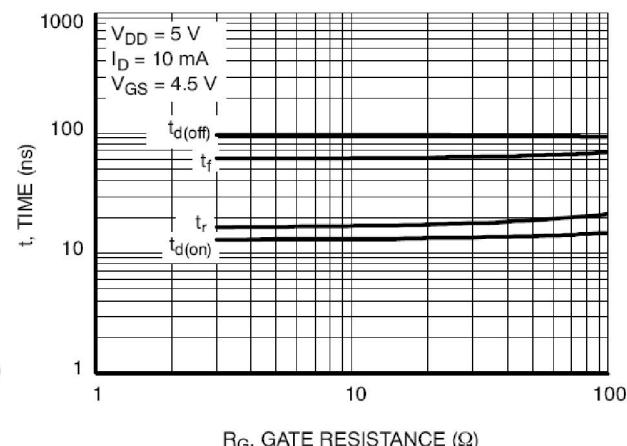
Figure 6. Drain-to-Source Leakage Current versus Voltage

## Typical Electrical and Thermal Characteristics

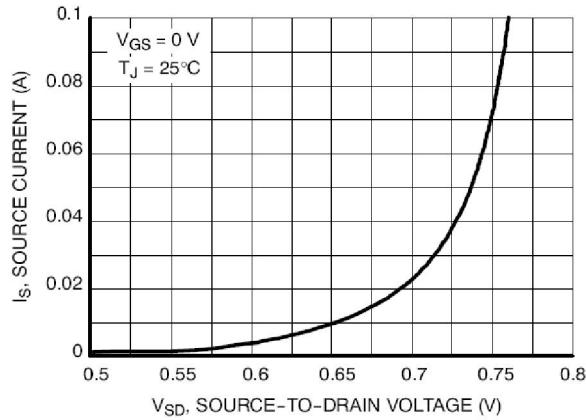


GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (V)

Figure 7. Capacitance Variation



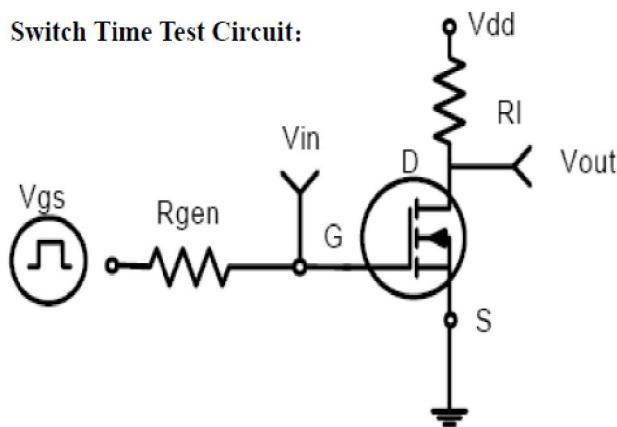
$R_G$ , GATE RESISTANCE (Ω)  
Figure 8. Resistive Switching Time Variation versus Gate Resistance



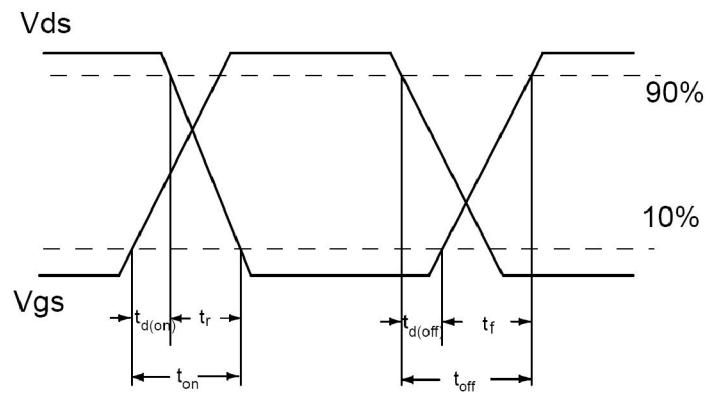
$I_S$ , SOURCE CURRENT (A)  
 $V_{SD}$ , SOURCE-TO-DRAIN VOLTAGE (V)  
Figure 9. Diode Forward Voltage versus Current

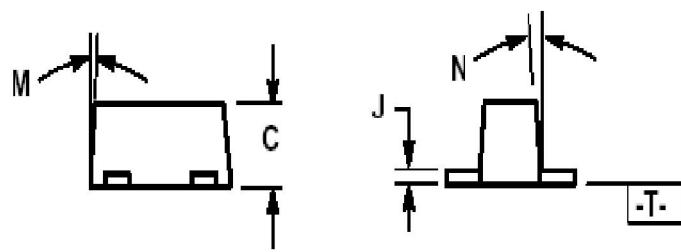
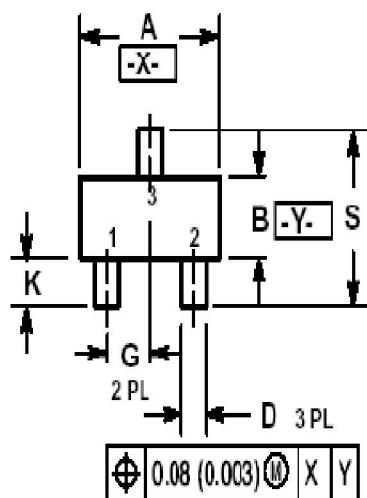
## Test Circuits and Waveforms

Switch Time Test Circuit:



Switch Waveforms:



**Mechanical Data(SC-89):**


DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
H	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
M	---	---	10°	---	---	10°
N	---	---	10°	---	---	10°
S	1.50	1.60	1.70	0.059	0.063	0.067

